

Si3861DV

Integrated Load Switch

General Description

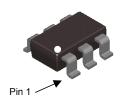
This device is particularly suited for compact power management in portable electronic equipment where 2.5V to 8V input and 2.8A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large P-Channel power MOSFET (Q2) in one tiny SuperSOTTM-6 package.

Applications

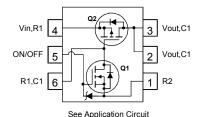
- · Load switch
- · Power management

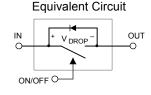
Features

- -2.8 A, -8 V. $R_{DS(ON)}$ = 55 m Ω @ V_{GS} = -4.5 V $R_{DS(ON)}$ = 70 m Ω @ V_{GS} = -2.5 V $R_{DS(ON)}$ = 100 m Ω @ V_{GS} = -1.8 V
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>6KV Human body model)
- High performance trench technology for extremely low $R_{\mathsf{DS}(\mathsf{ON})}$









Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{IN}	Maximum Input Voltage		± 8	V
V _{ON/OFF}	High level ON/OFF voltage range		-0.5 to 8	V
I _{Load}	Load Current - Continuous	(Note 1)	-2.8	Α
	Pulsed		-9	
P _D	Maximum Power Dissipation	(Note 1)	0.7	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1)	180	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.861	Si3861DV	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
BV _{IN}	Vin Breakdown Voltage	$V_{ON/OFF} = 0 \text{ V}, I_D = -250 \mu\text{A}$	8			V
I _{Load}	Zero Gate Voltage Drain Current	V _{IN} = 6.4 V, V _{ON/OFF} = 0 V			-1	μА
I _{FL}	Leakage Current, Forward	V _{ON/OFF} = 0 V, V _{IN} = 8 V			-100	nA
I _{RL}	Leakage Current, Reverse	$V_{ON/OFF} = 0 \text{ V}, V_{IN} = -8 \text{ V}$			100	nA
On Chai	racteristics (Note 2)		'		•	•
V _{ON/OFF (th)}	Gate Threshold Voltage	$V_{IN} = V_{ON/OFF}$, $I_D = -250 \mu A$	0.4	0.9	1.5	V
R _{DS(on)}	Static Drain-Source	$V_{IN} = 4.5 \text{ V}, \qquad I_{D} = -2.8 \text{A}$		34	55	mΩ
	On–Resistance (Q2)	$V_{IN} = 2.5 \text{ V}, \qquad I_D = -2.5 \text{ A}$		45	70	
		$V_{IN} = 1.8 \text{ V}, \qquad I_D = -2.0 \text{ A}$		64	100	
R _{DS(on)}	Static Drain-Source	$V_{IN} = 4.5 \text{ V}, \qquad I_D = 0.4 \text{A}$		3.1	4	Ω
	On–Resistance (Q1)	$V_{IN} = 2.7 \text{ V}, I_D = 0.2 \text{ A}$		3.8	5	

 V_{SD}

1. R $_{8JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R $_{8JC}$ is guaranteed by design while R $_{8JA}$ is determined by the user's board design.

 $V_{ON/OFF} = 0 \text{ V}, I_S = -0.6 \text{ A} \text{ (Note 2)}$

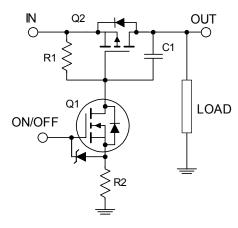
Maximum Continuous Drain-Source Diode Forward Current

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%.

Voltage

Si3861DV Load Switch Application Circuit

Drain-Source Diode Forward



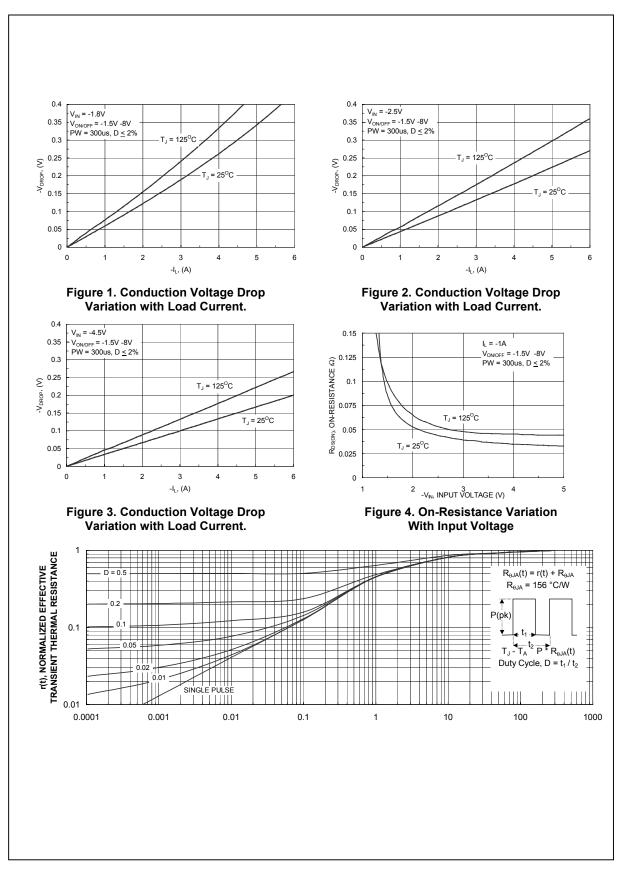
External Component Recommendation:

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030.

Si3861DV Rev B(W)

-0.6

-1.2



Si3861DV Rev B(W)

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